

Appl. No. 10/648,429  
Amdt. Dated May 23, 2006  
Reply to Office Action of February 23, 2006

Attorney Docket No. 81872.0050  
Customer No. 26021

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently amended) A dry etching method for fabricating a substrate, comprising:  
placing the substrate on an RF electrode in a chamber;  
placing a plate to cover the substrate, the plate being provided with a number of opening portions in a central region thereof and a number of opening portions in a peripheral region surrounding the central region thereof, an open area ratio of the opening portions in a the peripheral portion side of the plate region being smaller than an open area ratio of the opening portions in a the central portion region.
2. (Previously presented) The dry etching method according to Claim 1, wherein:  
the plate is placed to be spaced apart from the surface of the substrate by 5 to 30 nm.
3. (Previously presented) The dry etching method according to Claim 1, wherein:  
the substrate is a plate or a film member made of one material selected from silicon, glass, metal, plastic, and resin.
4. (Previously presented) The dry etching method according to Claim 1, wherein:  
the dry etching method is a reactive ion etching method.
- 5-7. (Canceled)

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8. (Currently amended) A dry etching method for fabricating a substrate, comprising:

placing the substrate on an RF electrode in a chamber;

placing a plate to cover the substrate while securing a distance from the surface of said substrate, the plate being provided with a number of opening portions, each opening portion being of a size such that allows a virtual column having a diameter equal to or less than half (1/2) the distance to pass through the opening portion while inhibiting a virtual column having a diameter greater than half the distance from passing through the opening portion;

~~introducing a gas inside said chamber.~~

9. (Previously presented) The dry etching method according to Claim 8, wherein:

the plate is placed to be spaced apart from the surface of the substrate by 5 to 30 mm.

10. (Previously presented) The dry etching method according to Claim 8, wherein:

the dry etching method is a reactive ion etching method.

11-14. (Canceled)

15. (Currently amended) A dry etching method for fabricating a substrate comprising:

placing the substrate on an RF electrode in a chamber;

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placing a plate to cover the substrate, said plate being provided with a number of opening portions, chamfered portions being provided to the top and/or bottom corners of the opening portions.

16-20. (Canceled)

21. (Currently amended) A dry etching method for fabricating a substrate, comprising:

placing the substrate on an RF electrode in a chamber;

placing a plate to cover the substrate, the plate being provided with a number of opening portions in a central region thereof and a number of opening portions in a peripheral region surrounding the central region thereof, an open area ratio of the opening portions in a the peripheral portion side of the plate region being smaller than an open area ratio of the opening portions in a the central portion region;

wherein a number of compounds are formed by an etching of the substrate during an RF power applying, wherein the compounds are trapped in a space between the substrate and the plate.

22. (Previously presented) The dry etching method according to claim 21, wherein:

the plate is placed to be spaced apart from the surface of the substrate by 5 to 30 mm.

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23. (Previously presented) The dry etching method according to claim 21,  
wherein:

the substrate is a plate or a film member made of one material selected from  
silicon, glass, metal, plastic and resin.

24. (Previously presented) The dry etching method according to claim 21,  
wherein

the dry etching method is a reactive ion etching method.

25. (Currently amended) A dry etching method for fabricating a substrate,  
comprising:

placing the substrate on an RF electrode in a chamber;

placing a plate to cover the substrate, the plate being provided with a number  
of opening portions in a central region thereof and a number of opening portions in  
a peripheral region surrounding the central region thereof, an open area ratio of the  
opening portions in a the peripheral portion side of the plate region being smaller  
than an open area ratio of the opening portions in a the central portion region;

wherein a number of compounds are formed by an etching of the substrate  
during an RF power applying, wherein the compounds are attached to the surface of  
the substrate.

26. (Previously presented) The dry etching method according to claim 25,  
wherein

the plate is placed to be spaced apart from the surface of the substrate by 5 to  
30 mm.

27. (Previously presented) The dry etching method according to claim 25,  
wherein

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the substrate is a plate or a film member made of one material selected from silicon, glass, metal, plastic and resin.

~~28~~ 29. (Currently amended) The dry etching method according to claim ~~29~~  
28, wherein

the dry etching method is a reactive ion etching method.

~~29~~ 28. (Currently amended) The dry etching method according to claim 1,  
comprising introducing a gas in a chamber; and  
applying an RF power supply to said RF electrode.

30. (Previously presented) The dry etching method according to claim 8,  
comprising introducing a gas in a chamber; and  
applying an RF power supply to said RF electrode.

31. (Previously presented) The dry etching method according to claim 15,  
comprising  
introducing a gas in a chamber; and  
applying an RF power supply to said RF electrode.

32. (New) The dry etching method according to claim 1, wherein the  
central region of the plate is opposed to a central region of the substrate, and the  
peripheral region of the plate is opposed to a peripheral region of the substrate.